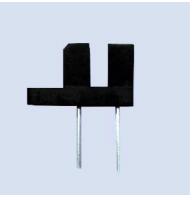


SGM8104

Technical Data Sheet Opto Interrupter SGM8104

Features

- Fast response time
- High analytic
- Peak wavelength $\lambda p=940 nm$
- High sensitivity
- Pb free



Descriptions

The SGM8104 consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black thermoplastic housing. The phototransistor receives radiation from the IR LED only. This is the normal situation. But when an object is in between , phototransistor could not receives the radiation.

Applications

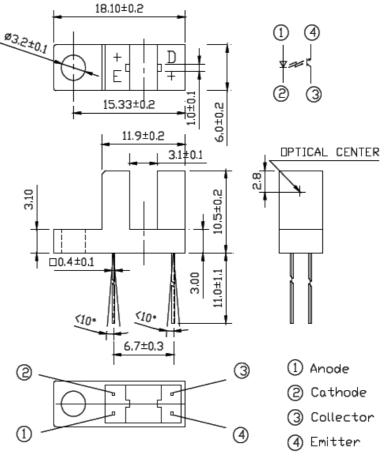
- Non-contact Switching
- Switch Scanner
- For Direct Board
- Floppy disk driver



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SGM8104

Package Dimensions



Notes:

- 1. All dimensions are in millimeters
- 2. Tolerances unless dimensions ±0.2mm
- 3. Lead spacing is measured where the lead emerge from the package

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	75	mW
	Reverse Voltage	V _R	5	V
	Forward Current	$I_{ m F}$	50	mA
	Peak Forward Current (*1) Pulse width $\leq 100 \mu$ s, Duty cycle=1%	I_{FP}	1	Α
Output	Collector Power Dissipation	Pd	75	mW
	Collector Current	I _C	20	mA
	Collector-Emitter Voltage	${ m B}~{ m V}_{ m CEO}$	30	V
	Emitter-Collector Voltage	$\mathbf{B} \mathbf{V}_{\mathrm{ECO}}$	5	v
Operating Temperature		Topr	-25~+85	°C
Storage Temperature		Tstg	-40~+85	°C
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		Tsol	260	°C

(*1) tw=100 μ sec., T=10 msec. (*2) t=5 Sec

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Electro-Optical Characteristics (1a=25 ()											
Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions				
	Forward Voltage	$V_{\rm F}$		1.2	1.5	V	I _F =20mA				
	Reverse Current	I _R			10	μA	V _R =5V				
Input	Peak Wavelength	λр		940		nm	I _F =20mA				
	View Angle	201/2		60		Deg	I _F =20mA				
	Dark C urrent	I _{CEO}			100	nA	V _{CE} =20V,Ee=0mW/cm ²				
Output	C-E Saturation Voltage	V _{CE} (sat)			0.4	v	I _C =2mA ,Ee=1mW/cm ²				
	Collect Current	I _C (ON)	0.5		10	mA	V _{CE} =5V				
Transfer	concer current	Ic(OFF)			20	μA	I _F =20mA				
Characteristics	Rise time	t _r		15		$\mu \sec$	V _{CE} =5V				
	Fall time	$t_{\rm f}$		15		$\mu \sec$	I _C =1mA				
							$R_L=1K\Omega$				

Electro-Optical Characteristics (Ta=25°C)

Typical Electrical/Optical/Characteristics Curves for IR

Fig.1 Forward Current vs.

Ambient Temperature

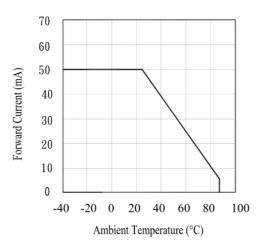
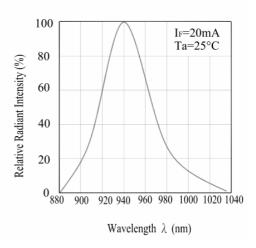
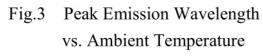


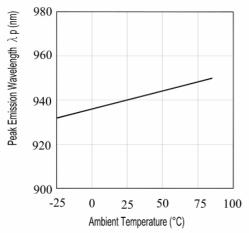
Fig.2 Spectral Distribution

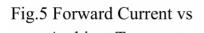


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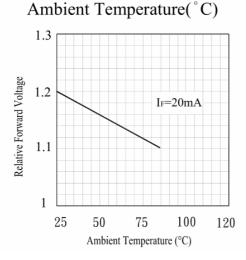


Fig.4 Forward Current

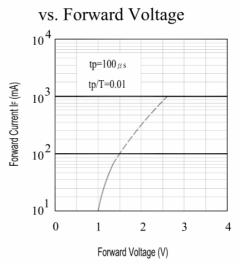
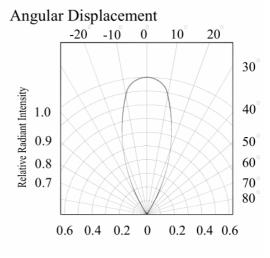


Fig.6 Relative Radiant Intensity vs.



Typical Electrical/Optical/Characteristics Curves for PT

Fig.1Collector Power Dissipation vs.

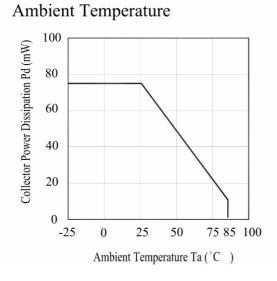
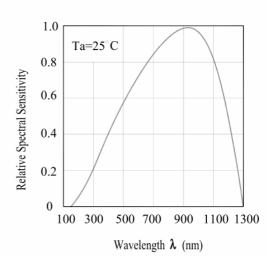
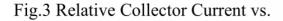


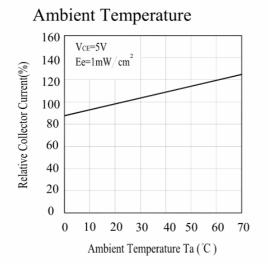
Fig.2 Spectral Sensitivity



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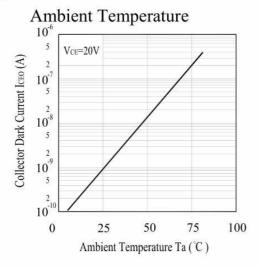
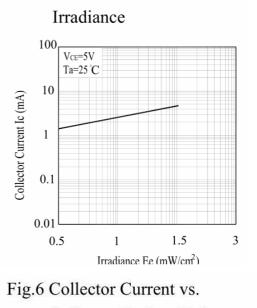
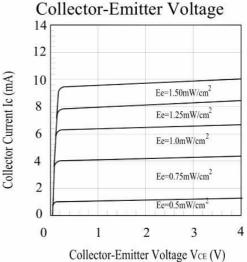


Fig.4 Collector Current vs.





Packing Quantity Specification

1. 100PCS/1Bag

Notes

- 1. Above specification may be changed without notice. SHUGUAN will reserve authority on material change for above specification.
- 2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. SHUGUAN assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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